

AMENDMENT

In the Specification:

Kindly amend paragraph [0001] as follows. No new matter has been introduced.

[0001] This application is also related to the following commonly assigned applications, entitled:

- (1) "Chemical Solution for Electroplating a Copper-Zinc Alloy Thin Film," concurrently filed (~~S/N to be assigned~~ US 10/081,074);
- (2) "Method of Electroplating a Copper-Zinc Alloy Thin Film on a Copper Surface Using a Chemical Solution and a Semiconductor Device thereby Formed," concurrently filed (~~S/N to be assigned~~ US 10/082,432);
- (3) "Method of Controlling Zinc-Doping in a Copper-Zinc Alloy Thin Film Electroplated on a Copper Surface and a Semiconductor Device thereby Formed," concurrently filed (~~S/N to be assigned~~ US 10/082,433);
- (4) "Method of Reducing Electromigration in a Copper Line by Electroplating an Interim Copper-Zinc Alloy Thin Film on a Copper Surface and a Semiconductor Device thereby Formed," concurrently filed ~~S/N to be assigned~~ (US 10/083,809);
- (5) "Method of Reducing Electromigration in a Copper Line by Zinc-Doping of a Copper Surface from an Electroplated Copper-Zinc Alloy Thin Film and a Semiconductor Device thereby Formed," filed on December 7, 2001, ~~U.S. Patent Application Serial No. (US 10/016,410; now issued as US 6,515,368)~~; and
- (6) "Method of Reducing Electromigration by Ordering Zinc-Doping in an Electroplated Copper-Zinc Interconnect and a Semiconductor Device thereby Formed," filed on December 7, 2001, ~~U.S. Patent Application Serial No. (US 10/016,645)~~.